CXG1017N

High-Frequency DPDT Antenna Switch

Description

The CXG1017N is a high power antenna switch MMIC. This IC is designed using the Sony's GaAs J-FET process and operates at a single positive power supply.

Features

- Single positive power supply operation
- Insertion loss 0.5dB (Typ.) at 1.5GHz
- High power switching

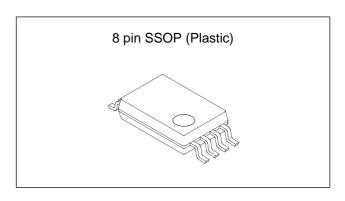
P1dB (Typ.) 33dBm at 2.0GHz VcTL (H) = 2.0V 36dBm at 2.0GHz VcTL (H) = 4.0V

Application

Antenna switch for digital cellular telephones

Structure

GaAs J-FET MMIC



Absolute Maximum Ratings (Ta = 25°C)

| Control voltage | VctI | 7 | V |
|---|------|-------------|----|
| Operating temperature | Topr | -35 to +85 | °C |
| Storage temperature | Tstg | -65 to +150 | °C |

Operating Condition

Control voltage 0/4 V

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Electrical Characteristics

Vctl (L) = 0V, Vctl (H) = 4V, Pin = 32dBm, Rrf = $75k\Omega$

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------------|--------|----------------|------|------|------|------|
| Insertion Loss | IL1 | f = 1.0GHz | | 0.4 | 0.7 | dB |
| Isolation | ISO1 | 1 = 1.0GHZ | 19 | 21 | | dB |
| Insertion Loss | IL1.5 | f = 1.5GHz | | 0.5 | 0.8 | dB |
| Isolation | ISO1.5 | T = 1.5GHZ | 16 | 18 | | dB |
| Insertion Loss | IL2 | | | 0.7 | 1.0 | dB |
| Isolation | ISO2 | f = 2.0GHz | 13 | 15 | | dB |
| VSWR | VSWR | | | | 1.5 | |
| Switching Time | TSW | | | 100 | | ns |

VCTL (L) = 0V, f = 2GHz

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|-----------------------|----------|----------------|------|------|------|------|
| 1dB Compression Point | P1dB (3) | Vctl (H) = 3V | 31 | 33 | | dBm |
| 1dB Compression Point | P1dB (4) | Vctl (H) = 4V | 34 | 36 | | dBm |

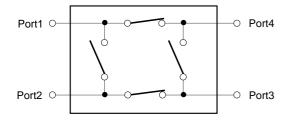
Vctl (L) = 0V, Rrf = 75k Ω

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|-----------------|----------|----------------|------|------|------|------|
| Control Current | Іст∟ (3) | VCTL (H) = 3V | | 130 | 160 | μΑ |
| Control Current | ICTL (4) | Vctl (H) = 4V | | 190 | 220 | μΑ |

Block Diagram

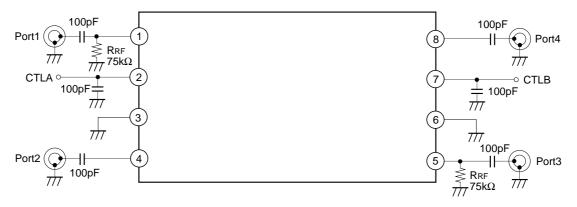




| Port1 (1) | (8) Port4 | | |
|---------------------|-----------|--|--|
| Politi | (a) F0114 | | |
| CTLA (2) | (7) CTLB | | |
| GND 3 | 6 GND | | |
| Port2 4 | 5 Port3 | | |
| | | | |
| 8pin SSOP (PLASTIC) | | | |

| VCTLA | Vстlв | |
|-------|-------|---|
| Hgh | Low | Port1-Port2, Port3-Port4 ON Port2-Port3, Port4-Port1 OFF |
| Low | High | Port2-Port3, Port4-Port1 ON Port1-Port2, Port3-Port4 OFF |

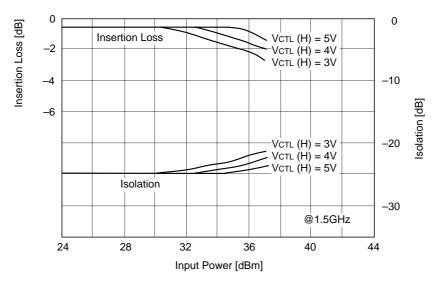
Recommended Circuit



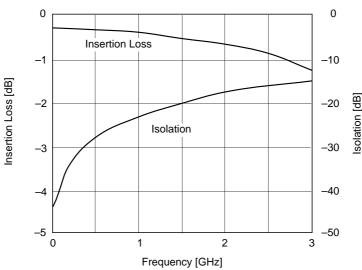
^{*} RRF is used to stabilize the electrical characteristics at high power signal input

Example of Representive Characteristics (Ta = 25°C)

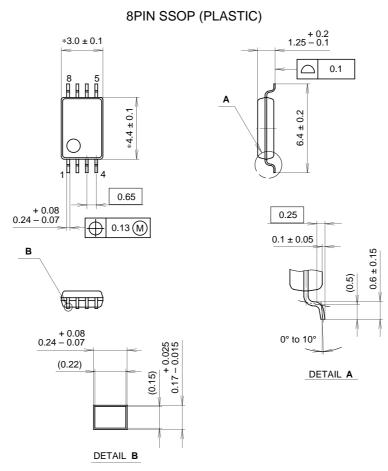
Insertion Loss and Isolation vs. Input Power



Insertion Loss and Isolation vs. Frequency



Package Outline Unit: mm



NOTE: Dimension "*" does not include mold protrusion.

| SONY CODE | SSOP-8P-L01 |
|------------|----------------|
| EIAJ CODE | SSOP008-P-0044 |
| JEDEC CODE | |

PACKAGE STRUCTURE

| PACKAGE MATERIAL | EPOXY RESIN |
|------------------|-------------------------------|
| LEAD TREATMENT | SOLDER / PALLADIUM PLATING |
| LEAD MATERIAL | COPPER ALLOY |
| PACKAGE WEIGHT | 0.04g |